AMENDMENTS TO THE SPECIFICATION

Please replace paragraph [0019] with the following amended paragraph:

[0019] After the high-k dielectric layer 180 is deposited, the structure shown in FIG. 1C is annealed to obtain the required structural and electrical properties. The annealing process forms an oxide layer 170 from oxidation of the surface portion 162 of the SiGe surface layer 160 that is in contact with the high-k dielectric layer 180. As a result, the oxide layer 170 is formed between the high-k dielectric layer 180 and the unreacted portion 164 or base portion of the SiGe surface layer 160. Alternatively, the oxide layer 170 can be formed during deposition of the high-k dielectric layer onto the SiGe surface layer or during both the deposition process and the annealing process. The presence of a SiGe surface layer 160 between the substrate 150 and the high-k dielectric layer 180 can prevent oxidation of the substrate 150.